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## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In the Application of:

Inventors : Alexander Leybovich  
Serial No. : 10/624,384  
Filed : July 22, 2003  
Title : Method and Apparatus for Deposition  
Of Low-K Dielectric Materials  
Docket No. : 020324 227P2  
Customer No.: 33805

**INFORMATION DISCLOSURE STATEMENT**

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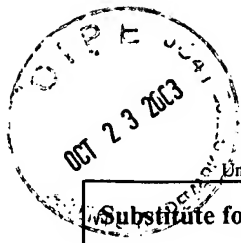
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Respectfully submitted,

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				<b>Application Number</b>	10/624,384
				<b>Filing Date</b>	July 22, 2003
				<b>First Named Inventor</b>	Leybovich
				<b>Art Unit</b>	
				<b>Examiner Name</b>	
<b>Sheet</b>	1	<b>of</b>	3	<b>Attorney Docket Number</b>	020324 227P2

**U.S. PATENT DOCUMENTS**

Examiner Initials*	Cite No. <sup>1</sup>	<u>Document Number</u> Number - Kind Code <sup>2</sup> (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
	AA	US-6,395,649	05-28-2002	Wu, Hui-Jung	
	AB	US-6,340,435	01-22-2002	Bjorkman et al.	
	AC	US-			
	AD	US-			
	AE	US-			
	AF	US-			
	AG	US-			
	AH	US-			
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**FOREIGN PATENT DOCUMENTS**

Examiner Initials*	Cite No. <sup>1</sup>	<u>Foreign Patent Document</u> Country - Number <sup>4</sup> - Kind Code <sup>5</sup> Code <sup>3</sup> (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T <sup>6</sup>

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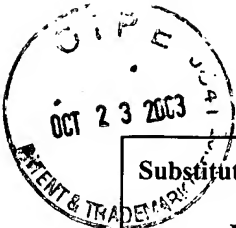
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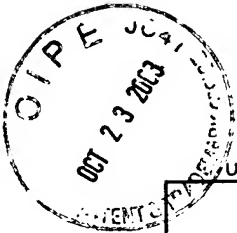
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	AJ	BALIGA, J.; Low-k Dielectrics Enable Faster Chips, Design News: Semiconductor Manufacturing, June 3, 2002, pp. S/13-S14			
	AK	CHAPMAN, B.; DC Glow Discharges, pp. 98-101			
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	AM	MAISSEL, Leon and GLANG, Reinhard; Handbook of Thin Film Technology, pp. 3-14—30-15, 3-24—3-27, 4-26—4-37, McGraw Hill Book Company			
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	AR	SHIMOKAWA, F. and NAGAI, K.; A Low-Energy Fast-Atom Source, Nuclear Instruments and Methods in Physics Research B33 (1988) pp. 867-870			
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	AU	GORBATOV, Y., VYATKIN, A. and ZINENKO, V.; A Low-Energy Fast-Atom Beam Source, Nuclear Instruments and Methods in Physics Research B55 (1991) 328-330	
	AV	Sputter Etching and Deposition of Insulators, pp. 195-197	
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	BA	YU et al.; Low K Film Etch in Applied Materials eMxP Plus Chamber; Materials Research Society Symposium - Proceedings, 1999 (Abstract)	
	BB	ZHANG et al.; Nanoglass/sup TM/E Copper Damascene Processing for Etch, Clean, and CMP; Proceedings of the IEEE 2001 International Interconnect Technology Conference 2001, pp. 57-9 (Abstract)	
	BC	BARSKAYA, A. YA. et al; Sputtering of Different Materials by Ions and Atoms, Journal of Technical Physics, v57, 6, 1987, pp 1223-1225 (Accompanied with two English abstracts)	

<b>Examiner Signature</b>		<b>Date Considered</b>	
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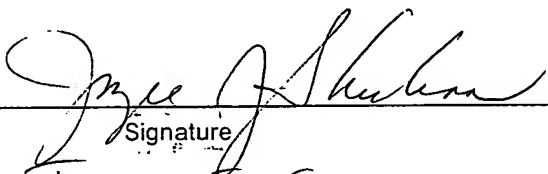
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